



PTO/SB/08b (08-03)

Approved for use through 06/30/2006. OMB 0551-0031
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete if Known			
		Application Number	10/500,214		
		Filing Date	June 28, 2004		
		First Named Inventor	Takuya SUGAWARA		
		Art Unit	2812 7823		
Sheet	1	of	1	Examiner Name	Francine Young Michelle Estrada
				Attorney Docket Number	010986.55104US

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	AA	Y. AOKI, ET AL., "In Situ Substrate Surface Cleaning by Low-Energy Ion Bombardment for High Quality Thin Film Formation", J. Vac. Sci. Technol. A, March/April 1993, pp. 307-313, vol. 11 no. 2, American Vacuum Society	
	AB	KATSUYUKI SEKINE, ET AL., "Silicon Nitride Film Growth for Advanced Gate Dielectric at Low Temperature Employing High-Density and low-Energy Ion Bombardment", J. Vac. Sci. Technol. A, September/October 1999, pp. 3129-3133, vol. 17, No. 5, American Vacuum Society	
	AC	KOTARO MIYATANI, ET AL., "A New Plasma Dry Cleaning Method Applied to Contact and Gate Pre Cleaning", Extended Abstracts of the 2002 International Conference on Solid State Devices and Materials, 2002, pp. 196-197, Nagoya	
	AD	N. SANO, ET AL., "Improvement of SiO ₂ /Si Interface by Low-Temperature Annealing in Wet Atmosphere", Appl. Phys. Lett., April 17, 1995, pp. 2107-2109, vol. 66, no. 16, American Institute of Physics	
	AE	D. TCHIKATKOV, ET AL., "Improvement of SiGe Oxide Grown by Electron Cyclotron Resonance Using H ₂ O Vapor Annealing", Appl. Phys. Lett., October 21, 1996, pp. 2578-2580, vol. 69, no. 17, American Institute of Physics	
	AF	TAKUYA SUGAWARA, ET AL., "Characterization of Ultra Thin Oxynitride Formed by Radical Nitridation with Slot Plane Antenna Plasma", Extended Abstracts of the 2002 International Conference on Solid Devices and Materials, 2002, pp. 714-715, Nagoya	
	AG	AKIKO NARA, ET AL., "A Guideline for Accurate Two-Frequency Capacitance Measurement for ultra-Thin Gate Oxides", Extended Abstracts of the 2002 International Conference on Solid Devices and Materials, 2002, pp. 452-453, Sendai	
	AH	ATSUHIRO TSUKUNE, ET AL., "Cu Damascene Formation Process", The 8 th Semiconductor Process Symposium, September 20, 1999, pp. 71-79	
	AI	T. NGAL ET AL., "Improving SiO ₂ /SiGe Interface of SiGe p-metal-oxide-silicon field-effect transistors using water vapor annealing", March 11, 2002, pp. 1773-1775	

Examiner Signature	Michelle Estrada	Date Considered	7/21/06
--------------------	------------------	-----------------	---------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.